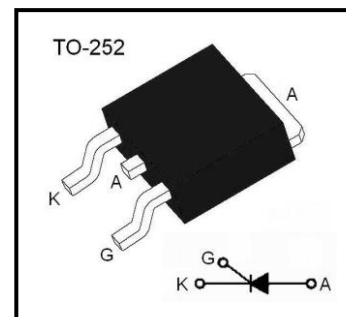


Silicon Controlled Rectifier Reverse Blocking Triode Thyristors

Passivated thyristors in a plastic envelope, intended for use in applications requiring high bidirectional blocking voltage capability and high thermal cycling performance. Typical applications include motor control, industrial domestic lighting, heating and static switching.



Absolute Maximum Rating (Ta=25°C)

Rating	Symbol	Value	Unit
Peak Repetitive Forward and Reverse Blocking Voltage	V_{DRM} V_{RRM}	400	V
RMS Forward Current (All Conduction Angles)	$I_{T(RMS)}$	2	A
Average Forward Current (TA = 30°C)	$I_{T(AV)}$	1.5	A
Peak Non-repetitive Surge Current	I_{TSM}	15	A
Peak Gate Power	P_{GM}	0.5	W
Peak Forward Gate Current	I_{GFM}	0.2	A
Operating Junction Temperature Range	T_J	-40 ~ +110	°C
Storage Temperature Range	Tstg	-40 ~ +150	°C

Electrical Characteristics (Ta=25°C)

Characteristic	Symbol	Test Conditions	Min	Typ	Max	Unit
Peak Forward or Reverse Blocking Current	I_{DRM} I_{RRM}	$V_D = V_{DRM}, V_R = V_{RRM}$			10	μA
On-State Voltage	V_{TM}	$I_T = 4 A$			1.7	V
Gate Trigger Current	I_{GT}	$V_D = 12 V; I_T = 0.1 A$		30	200	μA
Gate Trigger Voltage	V_{GT}	$V_D = 12 V; I_T = 0.1 A$			0.8	V
Holding Current	I_H	$V_D = 12 V; I_{GT} = 0.1 A$			3	mA
Forward Voltage Application Rate	dv/dt	$V_D = 60\% V_{DRM}, R_{GK} = 1K\Omega$			10	V/μs

**Package Dimensions** (unit:mm)